DRDO/ECE/2024-25/01/571-07

Project on
Design of S- and X-Band High Power Microwave Source- Relativistic Backward Wave Oscillator (RBWO)

DRDO DIA-COE Sponsored Project (No.: R&D/SA/DRDO/ECE/24-25/01/571)

DEPARTMENT OF ELECTRONICS ENGINEERING
INDIAN INSTITUTE OF TECHNOLOGY (BHU), VARANASI-221 005.

Advertisement for SRF & RA positions

Applications are invited from Indian nationals for the following positions in the research project entitled "**Design of S- and X- Band High Power Microwave Source- Relativistic Backward Wave Oscillator (RBWO)**" sponsored by the Defence Research & Development Organization (DRDO), through the DRDO Industry Academia (DIA) collaboration, Ministry of Defence, Government of India, New Delhi.

1. Senior Research Fellow (SRF) - Electronics Engineering

Name of the Position	Senior Research Fellow (SRF)
Number of Position(s)	Two (2)
Duration of the Project	Three Year. Initially the appointment will be made for one year and extendable on performance basis until the completion of project.
Emoluments	Rs. 42,000 + HRA @ 18 % per month (for I, II, & III Year)
Educational Qualification & Discipline	B.E./B.Tech., in Electronics and Communication Engineering or any allied discipline with first division and having valid GATE /NET score. (or) (i) M.E./M.Tech., in RF & Microwave Engineering, Applied Electronics, or any allied discipline with first division in both at Graduate and Post Graduate level & GATE Qualified is preferable.
Experience	Two years of experience as JRF in the area of RF and Microwave Engineering and related research field is mandatory.
Upper Age limit as on the last date of application	32 years. Age relaxation applicable as per Government of India (GoI) rules.

2. Research Associate (RA)- Electronics Engineering:

Name of the Position	Research Associate (RA)
Number of Position(s)	One (1)
Duration of the Project	Three Year. Initially the appointment will be made for one year and extendable up to three years on performance basis
Emoluments	Rs. 67,000 + HRA @ 18 % per month (for I, II, & III Year)
Educational Qualification	Ph.D. or equivalent degree in Electronics Engineering or having 3 years of research, teaching or design and development experience after M.E./M.Tech., (Electronics related area), with at least one research paper in Science Citation indexed (SCI) Journal.
Experience	Experience in the area of vacuum electronic high power microwave sources and amplifiers is desirable.
Upper Age limit as on the last date of application	35 years. Age relaxation applicable as per Government of India (GoI) rules.

General Terms and Conditions:

1. The position is purely temporary and is coterminous with the project.
2. The PI has the discretion to restrict the number of candidates to be called for interview to a reasonable limit on the basis of qualifications and experience higher than the minimum prescribed in the advertisement.
3. Only shortlisted candidates will be communicated to appear in the interview and no other communications in this regard will be entertained.
4. The candidate is expected to join immediately, if selected.
5. No TA/DA will be paid for attending the interview.

Application on Plain paper giving Name, Permanent and Correspondence address, Names of the Father and Mother, Telephone number. and e-mail address, details of educational career (starting from High School or equivalent) along with self-attested copies of all mark-sheets & certificates and details of any research or other experience, etc., if any, should reach the office of the **Principal Investigator** by **post or e-mail** on or before **28.07.2025.**

Prof. M. Thottappan,
Principal Investigator,
DRDO Sponsored Research Project,
Department of Electronics Engineering,
IIT (BHU), Varanasi-221005, Uttar Pradesh.
e-mail: mthottappan.ece@iitbhu.ac.in